TOSHIBA 2SD1508

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS) (DARLINGTON)

2SD1508

PULSE MOTOR DRIVE, HAMMER DIVE APPLICATIONS

SWITCHING APPLICATIONS

POWER AMPLIFIER APPLICATIONS

• High DC Current Gain

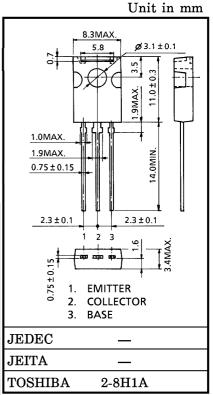
 $: h_{FE} = 4000 \text{ (Min.)}$

• Low Saturation Voltage

: $V_{CE (sat)} = 1.5V (Max.)$

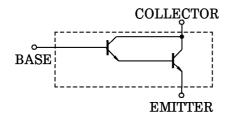
MAXIMUM RATINGS (Tc = 25°C)

CHARACTERIST	SYMBOL	RATING	UNIT		
Collector-Base Voltage		v_{CBO}	30	V	
Collector-Emitter Voltage		v_{CEO}	30	V	
Emitter-Base Voltage		v_{EBO}	10	V	
Collector Current	DC	$I_{\mathbf{C}}$	1.5	A	
	Pulse	I_{CP}	3.0		
Base Current		$I_{\mathbf{B}}$	50	mA	
Collector Power	$Ta = 25^{\circ}C$	1.2		w	
Dissipation	$Tc = 25^{\circ}C$	$_{\mathrm{PC}}$	10	**	
Junction Temperature		T_j	150	°C	
Storage Temperature Range		$\mathrm{T}_{\mathrm{stg}}$	-55~150	°C	



Weight: 0.72g (Typ.)

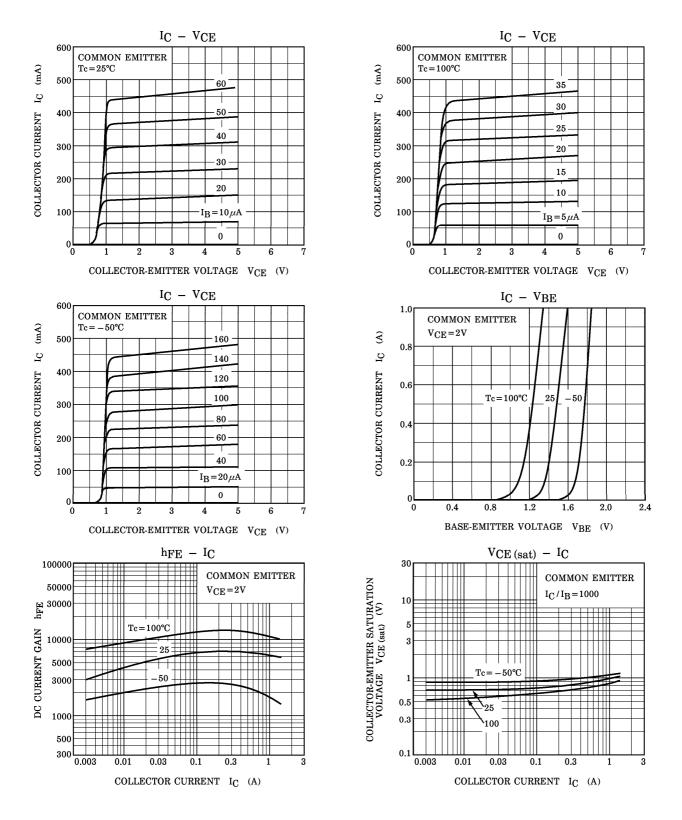
EQUIVALENT CIRCUIT



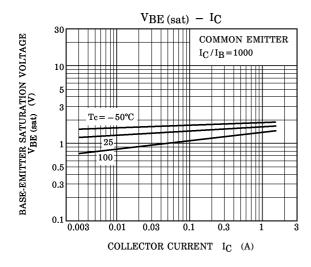
ELECTRICAL CHARACTERISTICS (Tc = 25°C)

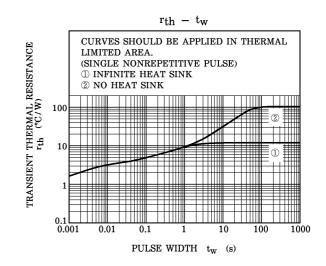
CHARAC	TERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 30V, I_{E} = 0$	_	_	10	μ A
Emitter Cut-off Current		$I_{ m EBO}$	$V_{EB} = 10V, I_{C} = 0$			10	μ A
Collector-Emit Voltage	ter Breakdown	V (BR) CEO	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	30	_	_	v
DC Current G	ain	$h_{ ext{FE}}$	$V_{CE}=2V, I_{C}=150mA$	4000	_	_	
Collector-Emit Voltage	ter Saturation	V _{CE} (sat)	I _C =1A, I _B =1mA	_		1.5	V
Base-Emitter Saturation Voltage		V _{BE} (sat)	I _C =1A, I _B =1mA	_		2.2	V
Switching Time Storag	Turn-on Time	ton	$I_{B1} \xrightarrow{I_{B1}} I_{B2}$ $I_{B1} = I_{B2} = 1_{MA}, V_{CC}$ $DUTY CYCLE \leq 1\%$ $OUTPUT$ C $DUTY CYCLE \leq 1\%$	_	0.18	_	
	Storage Time	$ m t_{stg}$		_	0.6	_	μs
	Fall Time	t_f		_	0.3	_	

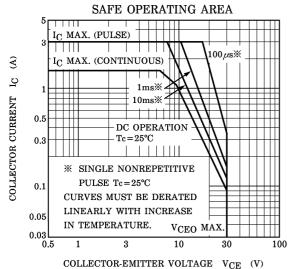
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